```
L3: (1) "5741735".PN.
L4: (1) "5834807".PN.
L5: (1) "6534817".PN.
L6: (1) "6534817".PN.
L7: (1) ("6214668").PN.
L8: (38802) flash adj memory
L9: (6443) 8 and (gate.clm.)
L10: (4630) 9 and (floating adj gate)
L11: (4035) 10 and (control adj gate)
L12: (983) 11 and (spacer$1 or sidewall$1 or
L13: (956) 12 and (source or drain)
L14: (572) 13 and photoresist and etch$3
L15: (554) 14 and (dopant$1 or doped or impla
L16: (507) 15 and (well or trench or junction
L17: (493) 16 and (flash.clm. or memory.clm.
L18: (398) 17 and (contact or (source adj lin
L19: (398) 18 and (etch$3 or pattern$3)
L20: (303) 18 and (etch$3 or pattern$3).clm.
L21: (241) 20 and (drain or source).clm.
L22: (8?) 21 and (second or another) near (p
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Failed
Saved

21 and ((second or another) near (photoresist or mask))

U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C			
	☑	☐	☐	US 20010024857	20010927		Novel flash integrated circuit and its method	438/259	438/257; 438/262;		Parat, Krishna et al.	☐	☐	☐	☐	
	☑	☐	☐	US 20010022375	20010920		Method to fabricate a new structure with mult	257/298	257/256; 257/314;		Hsieh, Chia-Ta et al.	☐	☐	☐	☐	
	☑	☐	☐	US 20010012662	20010809		A new structure to fabricate split-gate wi	438/257	257/E21.20 9;		Hsieh, Chia-Ta et al.	☐	☐	☐	☐	
	☑	☐	☐	US 20010001212	20010517		Flash memory structure using sidewall floating	257/315	257/E21.20 9;		Gambino, Jeffrey P. et al.	☐	☐	☐	☐	
	☐	☐	☐	US 6720216 B2	20040413	31	Method for forming a	438/257	257/314; 365/230.06		Forbes, Leonard	☑	☐	☐	☐	
	☐	☐	☐	US 6716699 B2	20040406	13	Method for manufacturing flash mem	438/257	438/265		Cho, Min-soo et al.	☑	☐	☐	☐	
	☐	☐	☐	US 6649471 B2	20031118	38	Method of planarizing non-volatile memory dev	438/257	438/697		Cho, Min-Soo et al.	☑	☐	☐	☐	
	☐	☐	☐	US 6638821 B1	20031028	20	Flash EEPROM with function of single bit	438/257	438/278		Hsieh, Chia-Ta	☑	☐	☐	☐	
	☐	☐	☐	US 6593187 B1	20030715	20	Method to fabricate a square poly spacer in f	438/257	257/296; 257/300; 257/315;		Hsieh, Chia-Ta	☑	☐	☐	☐	
	☐	☐	☐	US 6518123 B2	20030211	9	Split gate field effect transistor (FET) device	438/257	257/E21.20		Lin, Boson	☑	☐	☐	☐	
	☐	☐	☐	US 6461916 B1	20021008	114	Non-volatile semiconductor memory an	438/257	438/197		Adachi, Tetsuo et al.	☑	☐	☐	☐	
	☐	☐	☐	US 6380035	20020430	16	Poly tip formation and	438/264	257/E21.68		Sung, Hung-Cheng	☑	☐	☐	☐	